

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$ $T_C = +25^\circ C$
100V	5mΩ @ $V_{GS} = 10V$	140A

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

## Applications

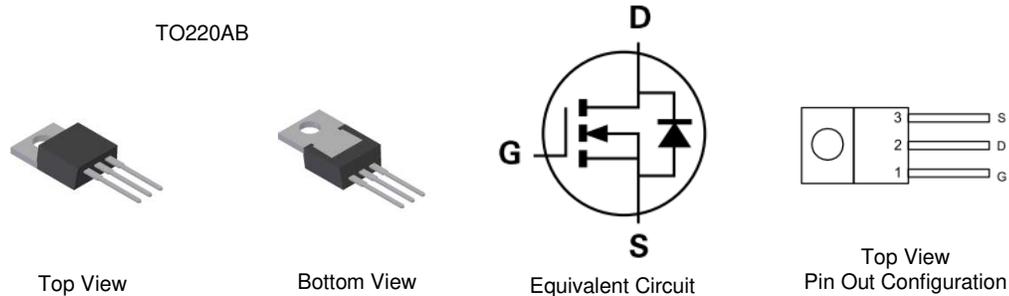
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low Input Capacitance
- High  $BV_{DSS}$  Rating for Power Application
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

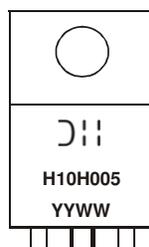


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H005LCT	TO220AB	50 Pieces/Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



- $\text{D}$  = Manufacturer's Marking
- H10H005 = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Last Two Digits of Year (ex: 16 = 2016)
- WW or WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> = +25°C	140
		T <sub>C</sub> = +100°C	99
Maximum Continuous Body Diode Forward Current	I <sub>S</sub>	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	150	A
Avalanche Current, L = 3mH (Note 7)	I <sub>AS</sub>	19	A
Avalanche Energy, L = 3mH (Note 7)	E <sub>AS</sub>	542	mJ
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	25	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	31.2	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.9	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	51	°C/W
Total Power Dissipation	P <sub>D</sub>	187	W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	0.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 6)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.4	1.9	3.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4	5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 13A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 13A
<b>DYNAMIC CHARACTERISTICS</b> (Note 7)						
Input Capacitance	C <sub>iss</sub>	—	3688	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	1494	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	48	—		
Gate Resistance	R <sub>G</sub>	—	0.75	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>G</sub>	—	114	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 13A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>GS</sub>	—	22.5	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	17.6	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	25	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 13A, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	26.9	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	83.6	—		
Turn-Off Fall Time	t <sub>F</sub>	—	53.1	—		
Reverse Recovery Time	t <sub>RR</sub>	—	65.5	—	ns	I <sub>F</sub> = 13A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	155.9	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

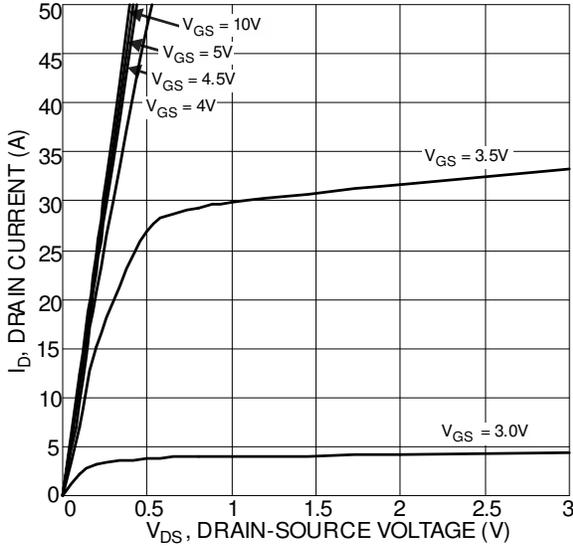


Figure 1 Typical Output Characteristic

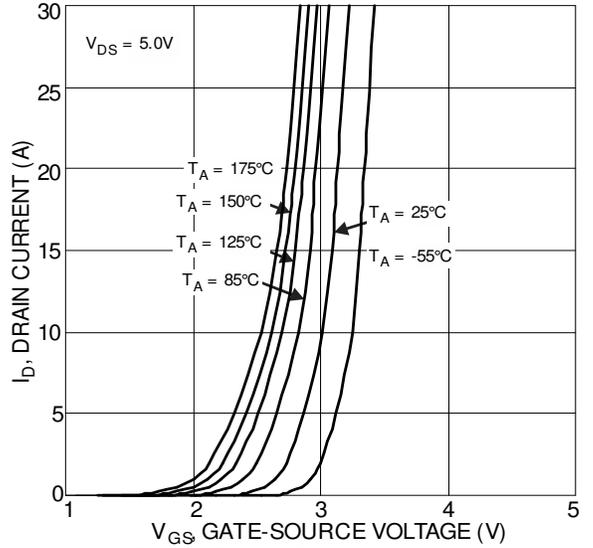


Figure 2 Typical Transfer Characteristics

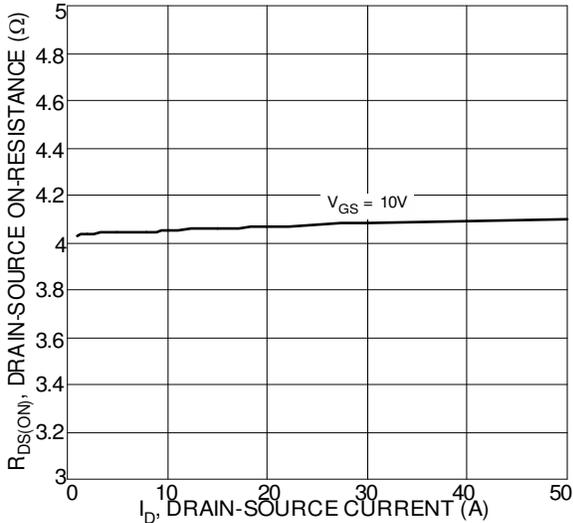


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

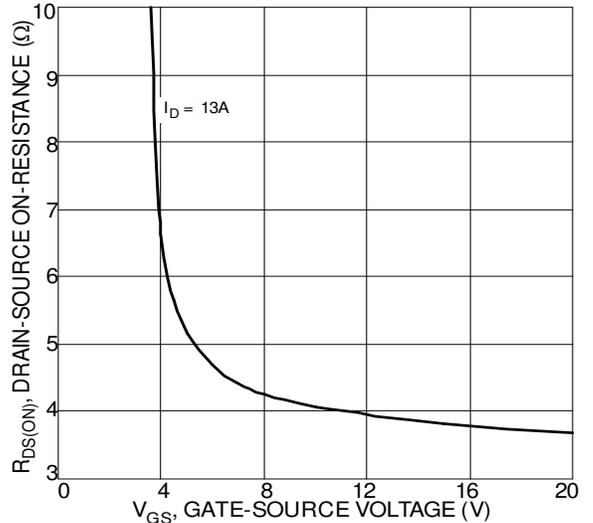


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

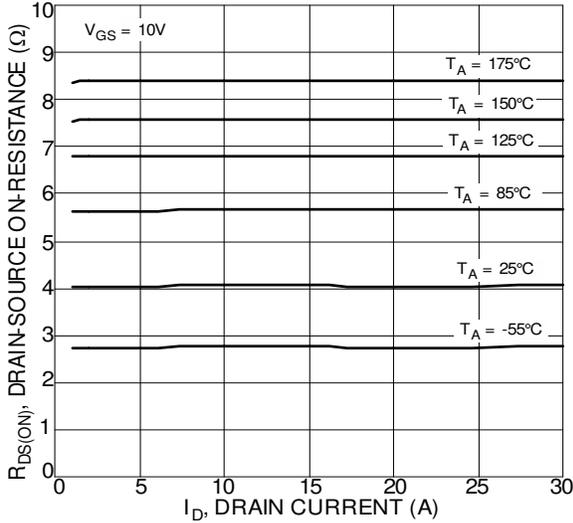


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

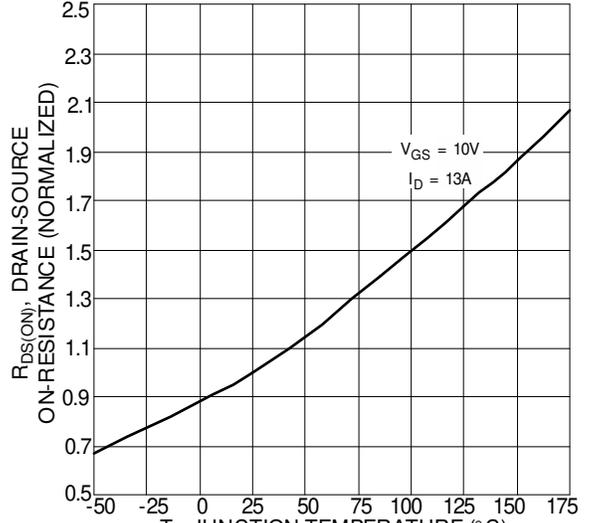


Figure 6 On-Resistance Variation with Temperature

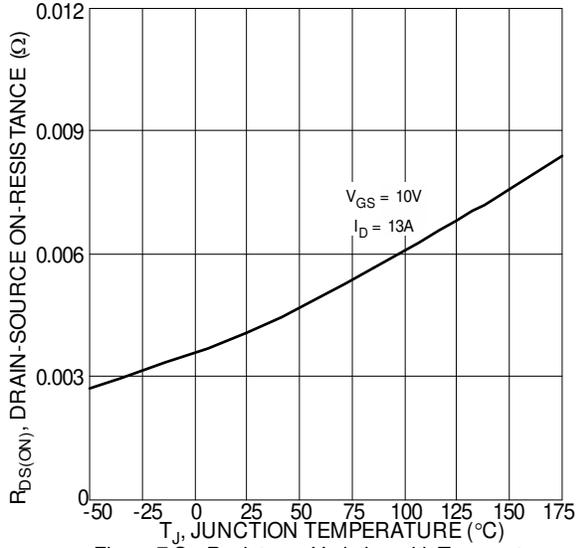


Figure 7 On-Resistance Variation with Temperature

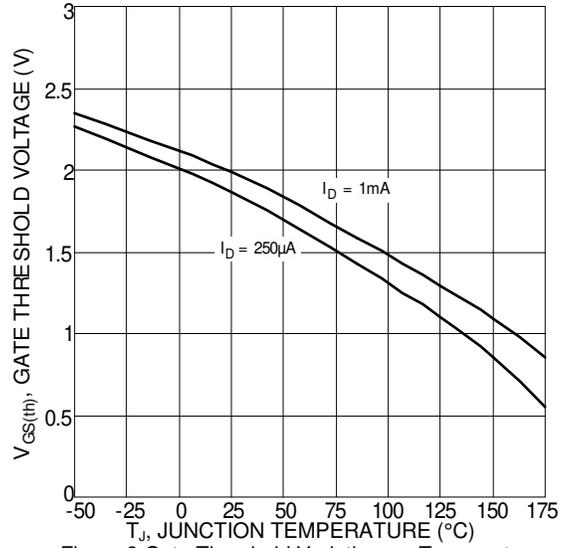


Figure 8 Gate Threshold Variation vs. Temperature

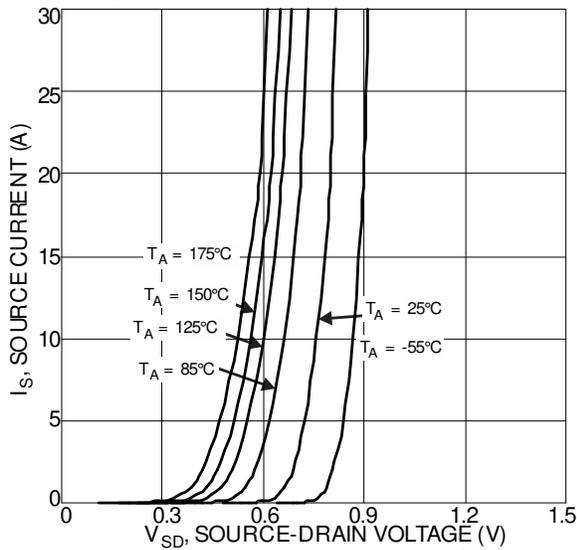


Figure 9 Diode Forward Voltage vs. Current

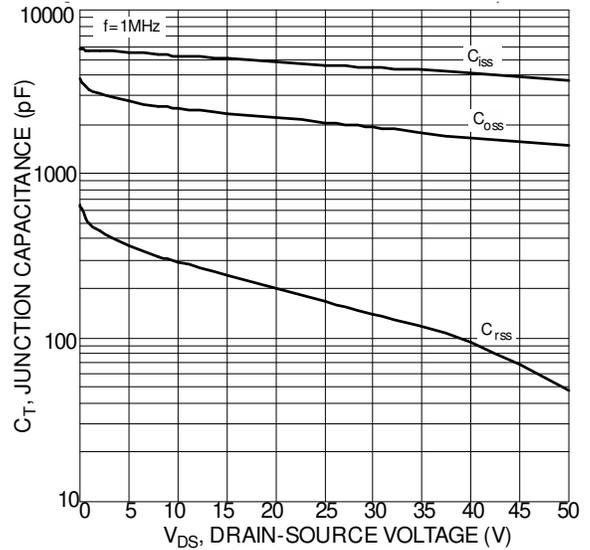


Figure 10 Typical Junction Capacitance

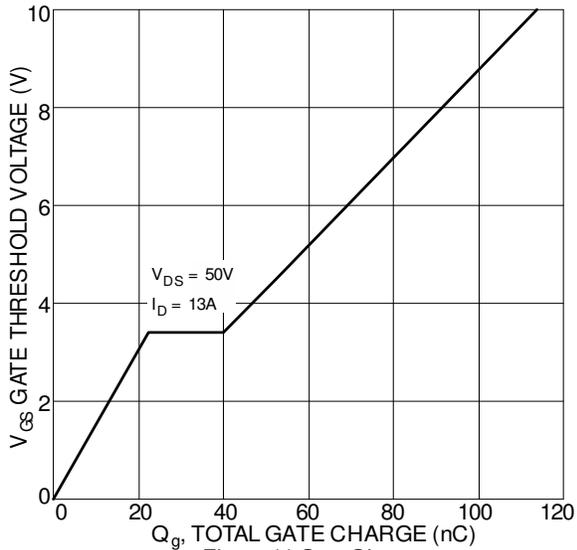


Figure 11 Gate Charge

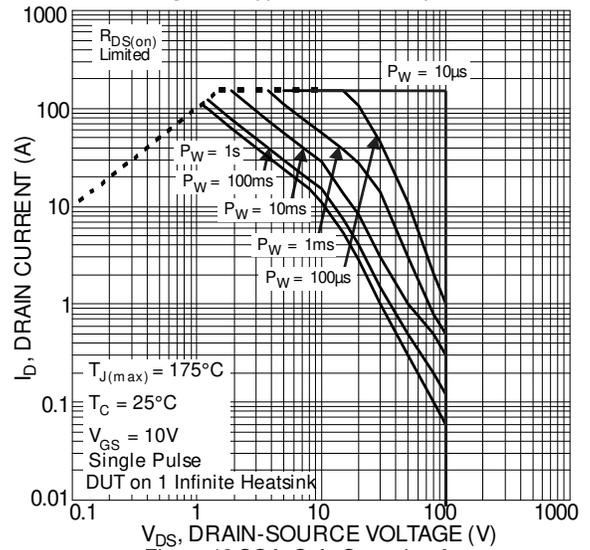
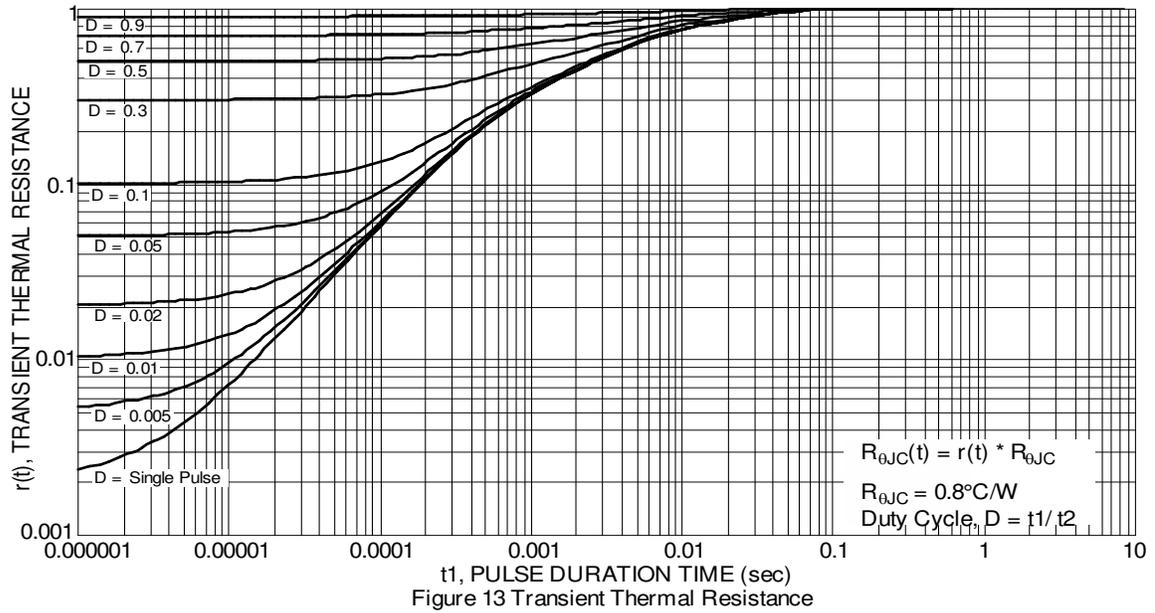


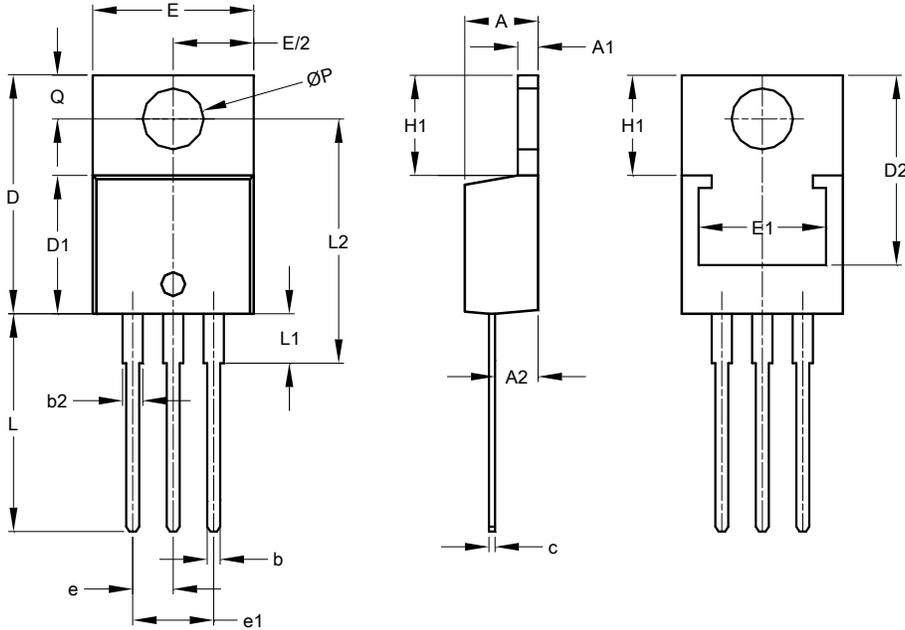
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO220AB**



TO220AB			
Dim	Min	Max	Typ
A	3.56	4.82	-
A1	0.51	1.39	-
A2	2.04	2.92	-
b	0.39	1.01	0.81
b2	1.15	1.77	1.24
c	0.356	0.61	-
D	14.22	16.51	-
D1	8.39	9.01	-
D2	11.45	12.87	-
e	-	-	2.54
e1	-	-	5.08
E	9.66	10.66	-
E1	6.86	8.89	-
H1	5.85	6.85	-
L	12.70	14.73	-
L1	-	4.42	-
L2	15.80	17.51	16.00
P	3.54	4.08	-
Q	2.54	3.42	-
All Dimensions in mm			

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